

# Rohit Khanna

## List of Publications by Year in descending order

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28  
papers

430  
citations

758635

12  
h-index

713013

21  
g-index

28  
all docs

28  
docs citations

28  
times ranked

483  
citing authors

#	ARTICLE	IF	CITATIONS
1	Inductively coupled plasma etch damage in (-201) Ga <sub>2</sub> O <sub>3</sub> Schottky diodes. Applied Physics Letters, 2017, 110, .	1.5	49
2	Annealing of dry etch damage in metallized and bare (-201) Ga <sub>2</sub> O <sub>3</sub> . Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	48
3	Thermal degradation of electrical properties and morphology of bulk single-crystal ZnO surfaces. Applied Physics Letters, 2004, 85, 3468-3470.	1.5	37
4	High dose Co-60 gamma irradiation of InGaN quantum well light-emitting diodes. Applied Physics Letters, 2005, 87, 212107.	1.5	35
5	Effects of high-dose 40MeV proton irradiation on the electroluminescent and electrical performance of InGaN light-emitting diodes. Applied Physics Letters, 2004, 85, 3131-3133.	1.5	32
6	Inductively coupled plasma etching of bulk, single-crystal Ga <sub>2</sub> O <sub>3</sub> . Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	32
7	W <sub>2</sub> B-based rectifying contacts to n-GaN. Applied Physics Letters, 2005, 87, 052110.	1.5	24
8	Comparison of CH <sub>4</sub> /H <sub>2</sub> and C <sub>2</sub> H <sub>6</sub> /H <sub>2</sub> inductively coupled plasma etching of ZnO. Applied Surface Science, 2006, 253, 1269-1273.	3.1	23
9	Proton irradiation of ZnO schottky diodes. Journal of Electronic Materials, 2005, 34, 395-398.	1.0	19
10	Dry etching of bulk single-crystal ZnO in CH <sub>4</sub> /H <sub>2</sub> -based plasma chemistries. Applied Surface Science, 2006, 253, 889-894.	3.1	16
11	Comparison of electrical and reliability performances of TiB <sub>2</sub> -, CrB <sub>2</sub> -, and W <sub>2</sub> B <sub>5</sub> -based Ohmic contacts on n-GaN. Journal of Vacuum Science & Technology B, 2006, 24, 744.	1.3	13
12	Improved thermally stable ohmic contacts on p-GaN based on W <sub>2</sub> B. Applied Physics Letters, 2006, 88, 012104.	1.5	13
13	Effects of high dose proton irradiation on the electrical performance of ZnO Schottky diodes. Physica Status Solidi A, 2004, 201, R79-R82.	1.7	12
14	Properties and annealing stability of Fe doped semi-insulating GaN structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2476-2479.	0.8	12
15	Thermal stability of W <sub>2</sub> B and W <sub>2</sub> B <sub>5</sub> contacts on ZnO. Applied Surface Science, 2005, 252, 1846-1853.	3.1	9
16	CrB <sub>2</sub> Schottky Barrier Contacts on n-GaN. Journal of the Electrochemical Society, 2005, 152, G804.	1.3	9
17	Annealing and measurement temperature dependence of W <sub>2</sub> B <sub>5</sub> -based rectifying contacts to n-GaN. Applied Surface Science, 2006, 252, 5814-5819.	3.1	9
18	Thermal stability of Ohmic contacts to InN. Applied Physics Letters, 2007, 90, 162107.	1.5	7

#	ARTICLE	IF	CITATIONS
19	Aging and Stability of GaN High Electron Mobility Transistors and Light-Emitting Diodes With $\text{TiB}_2$ - and Ir-Based Contacts. IEEE Transactions on Device and Materials Reliability, 2008, 8, 272-276.	1.5	7
20	ZrB <sub>2</sub> /Pt/Au Ohmic contacts on bulk, single-crystal ZnO. Applied Surface Science, 2006, 253, 2465-2469.	3.1	6
21	Dry etching of Ga <sub>2</sub> O <sub>3</sub> . , 2019, , 263-285.		5
22	Ir-Based Schottky and Ohmic Contacts on n-GaN. Journal of the Electrochemical Society, 2007, 154, H584.	1.3	4
23	Electrical and optical properties of p-GaN films implanted with transition metal impurities. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2520-2524.	0.8	3
24	Improved Thermal Stability CrB <sub>2</sub> Contacts on ZnO. Japanese Journal of Applied Physics, 2005, 44, 7291-7295.	0.8	3
25	Changes induced in electrical properties and deep level spectra of p-AlGa <sub>N</sub> films by treatment in hydrogen plasma and by proton implantation. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2480-2483.	0.8	1
26	Annealing temperature dependence of TiB <sub>2</sub> schottky barrier contacts on n-GaN. Journal of Electronic Materials, 2006, 35, 658-662.	1.0	1
27	Improved Long-Term Thermal Stability At 350°C Of TiB <sub>2</sub> -Based Ohmic Contacts On AlGa <sub>N</sub> /Ga <sub>N</sub> High Electron Mobility Transistors. Journal of Electronic Materials, 2007, 36, 379-383.	1.0	1
28	W <sub>2</sub> B based High Thermal Stability Ohmic Contacts to n-GaN. Materials Research Society Symposia Proceedings, 2005, 892, 307.	0.1	0